## A PA-CVD PROCESS FOR DEPOSITION OF A SOLID METAL-CONTAINING FILM ONTO A SUBSTRATE CONTAINING AT EAST 50 % of Fe or W.C

## PA-CVD PROCESS FOR DEPOSITION OF A SOUD METAL-CONTAINING FILM ONTO A SUBSTRATE CONTAINING AT 50 % of Fe or WC

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## Abstract

A new plasma assisted chemical vapour deposition (PA-CVD) process for deposition of a solid metal-containing film onto the surface of a substrate containing at least 50 % of Fe or WC (such as hard metal or steel), by which the metallic component of the metal-containing film is introduced into the system as a metal halide, is disclosed. The new process involves shifting the process gas composition between a high and a low metal halide level, whereby the adhesion of the deposited film to the substrate is improved.